SN74LVC1G06 Single Inverter Buffer/Driver With Open-Drain Output

1 Features

- ESD Protection Exceeds JESD 22
 - 2000-V Human Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)
- Available in the Texas Instruments NanoFree™ Package
- Supports 5-V V_{CC} Operation
- Input and Open-Drain Output Accept Voltages up to 5.5 V
- Maximum t_{pd} of 4.5 ns at 3.3 V at 125°C
- Low Power Consumption, 10-μA Maximum I_{CC}
- ±24-mA Output Drive at 3.3 V for open-drain devices
- I_{off} Supports Partial-Power-Down Mode and Back-Drive Protection
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- Can Be Used For Up or Down Translation
- Schmitt Trigger Action on All Ports

2 Applications

- AV Receivers
- Blu-ray Players and Home Theaters
- · DVD Recorders and Players
- Desktop or Notebook PCs
- · Digital Radio or Internet Radio Players
- Digital Video Cameras (DVC)
- Embedded PCs
- GPS: Personal Navigation Devices
- Mobile Internet Devices
- Network Projector Front-Ends
- Portable Media Plavers
- Pro Audio Mixers
- Smoke Detectors
- Solid State Drive (SSD): Enterprise
- High-Definition (HDTV)
- Tablets: Enterprise
- Audio Docks: Portable
- DLP Front Projection Systems
- DVR and DVS
- Digital Picture Frame (DPF)
- Digital Still Cameras

3 Description

This single inverter buffer and driver is designed for 1.65-V to 5.5-V V_{CC} operation.

NanoFree package technology is a major breakthrough in IC packaging concepts, using the die as the package.

The output of the SN74LVC1G06 device is opendrain and can be connected to other open-drain outputs to implement active-low wired-OR or activehigh wired-AND functions. The maximum sink current is 32 mA.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs when the device is powered down. This inhibits current backflow into the device which prevents damage to the device.

Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)					
SN74LVC1G06DBV	SOT-23 (5)	2.90 mm × 1.60 mm					
SN74LVC1G06DCK	SC70 (5)	2.00 mm × 1.25 mm					
SN74LVC1G06DRL	SOT-5X3 (5)	1.60 mm × 1.20 mm					
SN74LVC1G06DRY	SON (6)	1.45 mm × 1.00 mm					
SN74LVC1G06DSF	SON (6)	1.00 mm x 1.00 mm					
SN74LVC1G06YZP	DSBGA (5)	1.40 mm × 0.90 mm					
SN74LVC1G06YZV	DSBGA (4)	0.90 mm × 0.90 mm					
SN74LVC1G06DPW	X2SON (5)	0.80 mm x 0.80 mm					

For all available packages, see the orderable addendum at the end of the data sheet.

Logic Diagram (Positive Logic)



2

3

Features 1

Applications 1

Description 1

Table of Contents

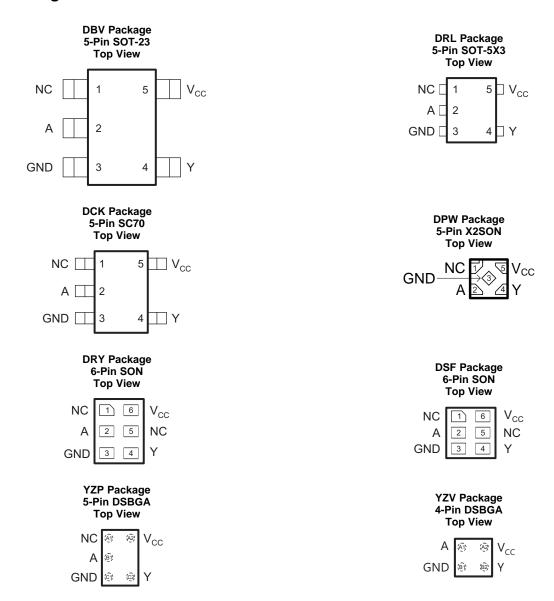
8.2 Functional Block Diagram9

8.4 Device Functional Modes...... 10

Feature Description......9

4 Revision History	2	9 Application	on and Implementation 1	1
_	nd Functions 3	9.1 Appli	cation Information1	1
_	4	9.2 Typic	al Application1	1
•	n Ratings4	10 Power St	upply Recommendations 1	3
	4	11 Layout	1	3
	perating Conditions5	11.1 Lay	out Guidelines1	3
	on 5	11.2 Lay	out Example1	3
	eristifcs6	12 Device a	nd Documentation Support 1	4
	eristics: -40°C to +85°C6	12.1 Rec	eiving Notification of Documentation Updates 1	4
· ·	eristics: -40°C to +125°C6	12.2 Con	nmunity Resources1	4
6.8 Operating Charact	teristics6		lemarks1	
6.9 Typical Characteri	stics 7	12.4 Elec	trostatic Discharge Caution1	4
7 Parameter Measure	ment Information8		ssary1	4
8 Detailed Description	ı 9		cal, Packaging, and Orderable	
•	9	Informati	on 1	4
Changes from Revision Y	(February 2017) to Revision Z		Pag	е
Changed values in the T	hermal Information table to align with	JEDEC standard	s	5
			S	
Updated Feature Descrip	otion to include more detailed informa	tion about specific	device features.	9
Updated Feature Descrip	otion to include more detailed informa	tion about specific		9
Updated Feature Descrip Added DPW layout exan	otion to include more detailed informa	tion about specific	device features 1	9
Updated Feature Descrip Added DPW layout exan	otion to include more detailed informa	tion about specific	device features.	9
Updated Feature Descript Added DPW layout exame Changes from Revision X	tion to include more detailed information to include more detailed information in the control of	tion about specific	device features 1	9 3 e
Updated Feature Descripe Added DPW layout exame Changes from Revision X Changed Logic Diagram	(August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3	to: A-2, Y-4	c device features 1	9 3 e 1
Updated Feature Descripe Added DPW layout exame Changes from Revision X Changed Logic Diagram	(August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3	to: A-2, Y-4	Pag	9 3 e 1
Updated Feature Descript Added DPW layout exame Changes from Revision X Changed Logic Diagram Added Receiving Notification	(August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3	to: A-2, Y-4	Pag	9 3 e 1 4
Changes from Revision X Changes from Revision X Changes from Revision X Changed Logic Diagram Added Receiving Notification Changes from Revision W Added Device Information table, Typical Characteri Implementation section,	(August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3 ation of Documentation Updates section (December 2013) to Revision X In table, Pin Configuration and Function stics section, Feature Description section Power Supply Recommendations sections	to: A-2, Y-4 onon ESD tion, Device Function, Layout section	Pag Ratings table, Thermal Information tional Modes, Application and	9 3 1 4 e
Changes from Revision X Changes from Revision X Changes from Revision X Changed Logic Diagram Added Receiving Notification Changes from Revision W Added Device Information table, Typical Characteri Implementation section,	(August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3 ation of Documentation Updates section (December 2013) to Revision X In table, Pin Configuration and Function stics section, Feature Description section Power Supply Recommendations sections	to: A-2, Y-4 onon ESD tion, Device Function, Layout section	Pag Ratings table, Thermal Information tional Modes, Application and on, Device and Documentation	9 3 e 1 4
Changes from Revision X Changes from Revision X Changes from Revision X Changed Logic Diagram Added Receiving Notification Changes from Revision W Added Device Information table, Typical Characteri Implementation section, Support section, and Me	(August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3 ation of Documentation Updates section (December 2013) to Revision X In table, Pin Configuration and Function stics section, Feature Description section Power Supply Recommendations sections	to: A-2, Y-4 onon ESD tion, Device Function, Layout section	Pag Ratings table, Thermal Information tional Modes, Application and on, Device and Documentation	9 3 e 1 4 e 1
Changes from Revision W Added Device Information table, Typical Characteri Implementation section, Support section, and Me Changes from Revision W	(August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3 ation of Documentation Updates section (December 2013) to Revision X In table, Pin Configuration and Function stics section, Feature Description section Power Supply Recommendations section, Packaging, and Orderable I	to: A-2, Y-4 on ons section, ESD tion, Device Function, Layout section formation section	Pag Ratings table, Thermal Information tional Modes, Application and on, Device and Documentation	9 3 1 4 1 e
Updated Feature Descript Added DPW layout exame Changes from Revision X and Changes from Revision Was Added Receiving Notifical Changes from Revision Was Added Device Information table, Typical Characterist Implementation section, Support section, and Me Changes from Revision Value	August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3 ation of Documentation Updates section (December 2013) to Revision X on table, Pin Configuration and Function stics section, Feature Description section Power Supply Recommendations section, Packaging, and Orderable I	to: A-2, Y-4 on ons section, ESD tion, Device Function, Layout section formation section	Pag Ratings table, Thermal Information tional Modes, Application and on, Device and Documentation Pag	9 3 e 1 e 1 e 1
Changes from Revision W Added Device Information table, Typical Characteri Implementation section, Support section, and Me Changes from Revision V Changes from Revision V Added Device Information table, Typical Characteri Implementation section, Support section, and Me Changes from Revision V Updated document to ne Removed Ordering Information	August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3 ation of Documentation Updates section (December 2013) to Revision X In table, Pin Configuration and Function stics section, Feature Description section Power Supply Recommendations section, Packaging, and Orderable I (November 2012) to Revision W In the Configuration and Function section (November 2012) to Revision W In the Configuration and I was a section of the Configura	to: A-2, Y-4 on ons section, ESD tion, Device Function, Layout section formation section	Pag Ratings table, Thermal Information tional Modes, Application and on, Device and Documentation Pag Pag	9 3 e 1 e 1 1 e 1 1
Changes from Revision X Changes from Revision X Changes from Revision X Changed Logic Diagram Added Receiving Notification Changes from Revision W Added Device Information table, Typical Characterial Implementation section, Support section, and Me Changes from Revision V Updated document to ne Removed Ordering Information Updated Ioff in Features.	(August 2015) to Revision Y (Positive Logic) labels from: A-1, Y-3 ation of Documentation Updates section (December 2013) to Revision X on table, Pin Configuration and Function stics section, Feature Description section (Power Supply Recommendations section), Packaging, and Orderable I (November 2012) to Revision W on TI data sheet format.	to: A-2, Y-4 on on pons section, ESD tion, Device Function, Layout section formation section	Pag Ratings table, Thermal Information tional Modes, Application and on, Device and Documentation Pag Pag	9 3 e 1 4 e 1 1 1 1

5 Pin Configuration and Functions



Pin Functions (1)(2)

		PIN					
NAME	DBV, DCK, DRL, DPW	DRY, DSF	YZP	YZV	I/O DESCRIPTION		I/O
Α	2	2	B1	A1	I	Input	
DNU	_	_	A1	_	_	Do not use	
GND	3	3	C1	B1	_	Ground	
NO	4	1				Matanasatad	
NC	1	5		_	_	Not connected	
V _{CC}	5	6	A2	A2	_	Power pin	
Υ	4	4	C2	B2	0	Output	

- (1) NC No internal connection
- (2) See mechanical drawings for dimensions.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		-0.5	6.5	V
VI	Input voltage (2)		-0.5	6.5	V
Vo	Voltage applied to any output in the high-impedance or	power-off state (2)	-0.5	6.5	V
Vo	Voltage applied to any output in the high or low state (2)	(3)	-0.5	6.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±50	mA
	Continuous current through V _{CC} or GND			±100	mA
Tj	Junction temperature		-65	150	°C
T _{stg}	Storage temperature		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
		Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	2000	
$V_{(ESD)}$	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	1000	V
		Machine Model (MM), per A115-A	200	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

⁽²⁾ The input and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the *Recommended Operating Conditions* table.

⁽²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT	
.,	Complements	Operating	1.65	5.5	V	
V_{CC}	Supply voltage	Data retention only	1.5		V	
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}			
\	High lavel inner college	V _{CC} = 2.3 V to 2.7 V	1.7		.,	
V_{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V	
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}			
		V _{CC} = 1.65 V to 1.95 V	to 1.95 V 0.35 × V _{CC}			
.,	Lauria de la lauria de la cara	V _{CC} = 2.3 V to 2.7 V		0.7	.,	
V _{IL} Low	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V	
		V _{CC} = 4.5 V to 5.5 V		0.3 × V _{CC}		
VI	Input voltage		0	5.5	V	
Vo	Output voltage		0	5.5	V	
		V _{CC} = 1.65 V		4		
		V _{CC} = 2.3 V		8		
I_{OL}	Low-level output current	V 2V		16	mA	
		V _{CC} = 3 V		24		
		V _{CC} = 4.5 V		32		
		V _{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20		
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V	
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5	-	
T _A	Operating free-air temperature		-40	125	°C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See *Implications of Slow or Floating CMOS Inputs* application report.

6.4 Thermal Information

	THERMAL METRIC ⁽¹⁾			SI	N74LVC1G0	6			
THE			DCK (SC70)	DRL (SOT-5X3)	DRY (SON)	DPW (X2SON)	YZV (DSBGA)	YZP (DSBGA)	UNIT
		5 PINS	5 PINS	5 PINS	5 PINS	5 PINS	4 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	231.5	276.1	296.2	369.6	511	168.2	144.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	139.4	178.9	137.3	257.6	241.9	2.1	1.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	71.1	70.9	145.3	230.8	374.2	55.9	39.9	°C/W
ΨЈТ	Junction-to-top characterization parameter	45.2	47	14.7	77.2	45	1.1	0.5	°C/W
ΨЈВ	Junction-to-board characterization parameter	70.7	69.3	145.9	231	373.3	56.3	39.7	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	168	N/A	N/A	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metricsapplication report.

6.5 Electrical Characteristifcs

over recommended operating free-air temperature range (unless otherwise noted)

PA	RAMETER	TEST CONDITIONS		V _{cc}	MIN	TYP ⁽¹⁾	MAX	UNIT
		I _{OL} = 100 μA		1.65 V to 5.5 V			0.1	
		I _{OL} = 4 mA	I _{OL} = 4 mA				0.45	
.,	High-level V _{OI} output	I _{OL} = 8 mA		2.3 V			0.3	V
V _{OL}	voltage	I _{OL} = 16 mA		3 V			0.4	V
	· ·	I _{OL} = 24 mA		3 V			0.55	
		I _{OL} = 32 mA		4.5 V			0.55	
II	Inflection- point current	V _I = 5.5 V or GND	A input	0 to 5.5 V			±1	μΑ
I _{off}	Off-state current	V_I or $V_O = 5.5 \text{ V}$		0			±10	μΑ
I _{CC}		$V_I = 5.5 \text{ V or GND}, I_O = 0$		1.65 V to 5.5 V			10	μΑ
ΔI_{CC}		One input at $V_{CC} - 0.6 \text{ V}$, Other inputs at V_{CC} or GND		3 V to 5.5 V			500	μΑ
Cı	Input capacitance	$V_I = V_{CC}$ or GND		3.3 V		4		pF
Co	Off-state capacitance	$V_{O} = V_{CC}$ or GND	_	3.3 V	·	5		pF

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

6.6 Switching Characteristics: -40°C to +85°C

over recommended operating free-air temperature range, $T_A = -40$ °C to +85°C (unless otherwise noted) (see Figure 3)

	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{cc}	MIN	MAX	UNIT
				$1.8 \text{ V} \pm 0.15 \text{ V}$	2.2	6.5	
	Propagation	^	V	2.5 V ± 0.2 V	1.1	4	
^L pd	Propagation delay	A	Ť	$3.3 \text{ V} \pm 0.3 \text{ V}$	1.2	4	ns
				5 V ± 0.5 V	1	3	

6.7 Switching Characteristics: -40°C to +125°C

over recommended operating free-air temperature range, $T_A = -40$ °C to +125°C (unless otherwise noted) (see Figure 3)

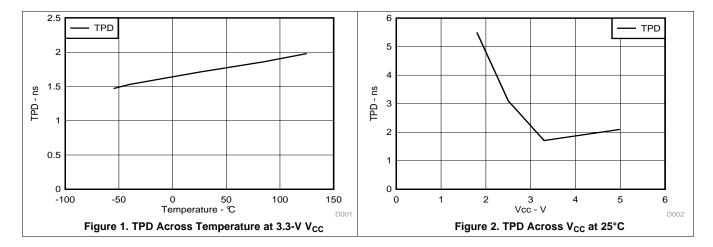
	PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC}	MIN	MAX	UNIT
				1.8 V ± 0.15 V	2.2	7	
	Propagation	٨	V	2.5 V ± 0.2 V	1.1	4.5	
^L pd	delay	A	Y	3.3 V ± 0.3 V	1.2	4.5	ns
				5 V ± 0.5 V	1	3.5	

6.8 Operating Characteristics

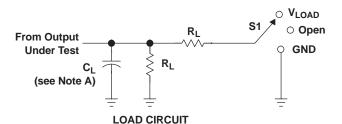
 $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{CC}	TYP	UNIT
		1.8 V	3		
_	C _{pd} Power dissipation capacitance	f = 10 MHz	2.5 V	3	~F
C_{pd}		I = IU IVIMZ	3.3 V	4	pF
			5 V	6	

6.9 Typical Characteristics

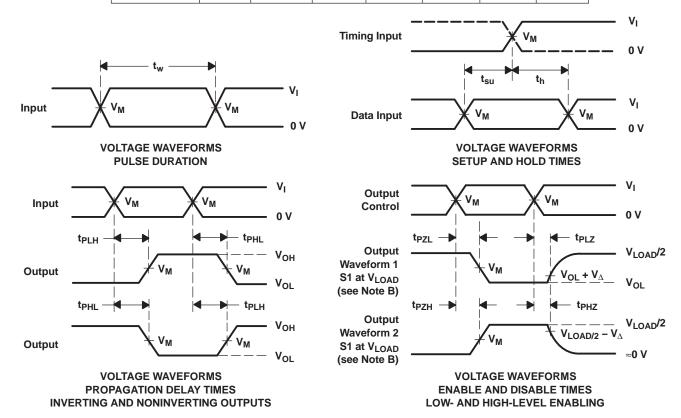


7 Parameter Measurement Information



TEST	S 1
t _{PZL} (see Notes E and F)	V_{LOAD}
t _{PLZ} (see Notes E and G)	V_{LOAD}
t _{PHZ} /t _{PZH}	V_{LOAD}

	INPUT V _I t _r /t _f						
V _{CC}			V _M	V _{LOAD}	CL	R _L	V_Δ
1.8 V \pm 0.15 V	V _{CC}	≤ 2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	V _{CC}	≤ 2 ns	V _{CC} /2	2×V _{CC}	30 pF	500 Ω	0.15 V
3.3 V \pm 0.3 V	3 V	≤ 2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V \pm 0.5 V	V _{CC}	≤ 2.5 ns	V _{CC} /2	2 × V _{CC}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_0 = 50 \ \Omega$.
- D. The outputs are measured one at a time, with one transition per measurement.
- E. Since this device has open-drain outputs, t_{PLZ} and t_{PZL} are the same as t_{pd}.
- F. t_{PZL} is measured at V_{M} .
- G. t_{PLZ} is measured at $V_{OL} + V_{\Delta}$.
- H. All parameters and waveforms are not applicable to all devices.

Figure 3. Load Circuit and Voltage Waveforms (Open Drain)

8 Detailed Description

8.1 Overview

The SN74LVC1G06 device contains one open-drain inverter with a maximum sink current of 32 mA. This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs when the device is powered down. This inhibits current backflow into the device which prevents damage to the device.

8.2 Functional Block Diagram

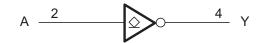


Figure 4. Logic Diagram (Positive Logic)

8.3 Feature Description

8.3.1 CMOS Open-Drain Outputs

The open-drain output allows the device to sink current to GND but not to source current from V_{CC} . When the output is not actively pulling the line low, it will go into a high impedance state (tri-state). This allows the device to be used for a wide variety of applications, including up-translation and down-translation, as the output voltage can be determined by an external pullup.

The drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the power output of the device to be limited to avoid thermal runaway and damage due to over-current. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

8.3.2 Standard CMOS Inputs

The impendence for standard CMOS inputs is high. Typically, a CMOS input is modeled as a resistor in parallel with the input capacitance as shown in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using ohm's law $(R = V \div I)$.

Signals applied to the inputs need to have fast edge rates, as defined by $\Delta t/\Delta v$ in the *Recommended Operating Conditions* to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal before the standard CMOS input.

Feature Description (continued)

8.3.3 Negative Clamping Diodes

The inputs and outputs to this device have negative clamping diodes as depicted in Figure 5.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input negative-voltage and the output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

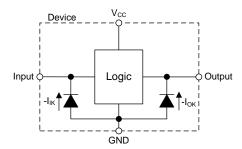


Figure 5. Electrical Placement of Clamping Diodes for Each Input and Output

8.3.4 Partial Power Down (I_{off})

Each input and output enter a high impedance state when the supply voltage is 0 V. The maximum leakage into or out of any input or output pin on the device is specified by I_{off} in the *Electrical Characteristics*.

8.3.5 Over-voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage as long as the input signals remain below the maximum input voltage value specified in the *Recommended Operating Conditions*.

8.4 Device Functional Modes

Table 1 lists the functional modes of the SN74LVC1G06.

Table 1. Function Table

INPUT A	OUTPUT Y
L	Hi-Z
Н	L

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The SN74LVC1G06 is a high-drive CMOS device that can be used to implement a high output drive buffer, such as an LED application. It can sink 32 mA of current at 4.5 V making it ideal for high-drive applications. It is good for high-speed applications up to 100 MHz. The inputs are 5.5-V tolerant allowing it to translate up or down to V_{CC} . Below shows a simple LED driver application for a single channel of the device.

9.2 Typical Application

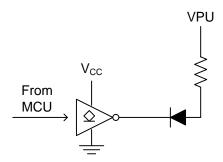


Figure 6. Typical Application Diagram

9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

9.2.2 Detailed Design Procedure

- 1. Recommended Input Conditions
 - Rise time and fall time specs. See $(\Delta t/\Delta V)$ in the *Recommended Operating Conditions* table.
 - Specified high and low levels. See (V_{IH} and V_{IL}) in the Recommended Operating Conditions table.
 - Inputs are overvoltage tolerant allowing them to go as high as (V_I max) in the Recommended Operating
 Conditions table at any valid V_{CC}.
- 2. Recommended Output Conditions
 - Load currents should not exceed (I_O max) per output and should not exceed (Continuous current through V_{CC} or GND) total current for the part. These limits are located in the *Absolute Maximum Ratings* table.
 - Outputs should not be pulled above 5.5 V.

Typical Application (continued)

9.2.3 Application Curve

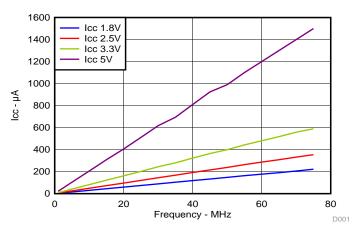


Figure 7. I_{CC} vs Frequency

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions* table.

The V_{CC} pin must have a good bypass capacitor to prevent power disturbance. A 0.1- μ F capacitor is recommended, and it is ok to parallel multiple bypass caps to reject different frequencies of noise. 0.1- μ F and 1- μ F capacitors are commonly used in parallel. The bypass capacitor must be installed as close to the power pin as possible for best results.

11 Layout

11.1 Layout Guidelines

Even low data rate digital signals can contain high-frequency signal components due to fast edge rates. When a printed-circuit board (PCB) trace turns a corner at a 90° angle, a reflection can occur. A reflection occurs primarily because of the change of width of the trace. At the apex of the turn, the trace width increases to 1.414 times the width. This increase upsets the transmission-line characteristics, especially the distributed capacitance and self–inductance of the trace which results in the reflection. Not all PCB traces can be straight and therefore some traces must turn corners. Figure 8 shows progressively better techniques of rounding corners. Only the last example (BEST) maintains constant trace width and minimizes reflections.

An example layout is given in Figure 9 for the DPW (X2SON-5) package. This example layout includes a 0402 (metric) capacitor and uses the measurements found in the example board layout appended to this end of this datasheet. A via of diameter 0.1 mm (3.973 mil) is placed directly in the center of the device. This via can be used to trace out the center pin connection through another board layer, or it can be left out of the layout

11.2 Layout Example

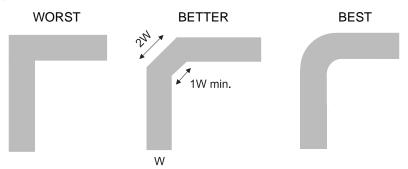


Figure 8. Trace Example

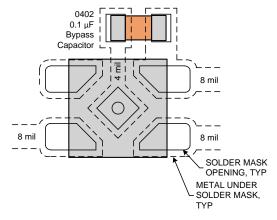


Figure 9. Example Layout With DPW (X2SON-5) Package

12 Device and Documentation Support

12.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community.* Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

12.3 Trademarks

NanoFree, E2E are trademarks of Texas Instruments. All other trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

12.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

PACKAGE OPTION ADDENDUM

10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan			Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC1G06DBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C065, C06F, C06J, C06R, C06T) (C06H, C06P, C06S)	Samples
SN74LVC1G06DBVRE4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C06F	Samples
SN74LVC1G06DBVRG4	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C06F	Samples
SN74LVC1G06DBVT	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C065, C06F, C06J, C06R) (C06H, C06P, C06S)	Samples
SN74LVC1G06DBVTG4	ACTIVE	SOT-23	DBV	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C06F	Samples
SN74LVC1G06DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CT5, CTF, CTK, CT R, CTT) (CTH, CTS)	Samples
SN74LVC1G06DCKRE4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CT5, CTF, CTK, CT R, CTT) (CTH, CTS)	Samples
SN74LVC1G06DCKRG4	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CT5, CTF, CTK, CT R, CTT) (CTH, CTS)	Samples
SN74LVC1G06DCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CT5, CTF, CTK, CT R) (CTH, CTS)	Samples
SN74LVC1G06DCKTE4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CT5, CTF, CTK, CT R) (CTH, CTS)	Samples
SN74LVC1G06DCKTG4	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	(CT5, CTF, CTK, CT R) (CTH, CTS)	Samples
SN74LVC1G06DPWR	ACTIVE	X2SON	DPW	5	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	СО	Samples
SN74LVC1G06DRLR	ACTIVE	SOT-5X3	DRL	5	4000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	(CT7, CTR)	Samples

PACKAGE OPTION ADDENDUM

10-Dec-2020

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74LVC1G06DRYR	ACTIVE	SON	DRY	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	СТ	Samples
SN74LVC1G06DSFR	ACTIVE	SON	DSF	6	5000	RoHS & Green	NIPDAU NIPDAUAG	Level-1-260C-UNLIM	-40 to 125	СТ	Samples
SN74LVC1G06YZPR	ACTIVE	DSBGA	YZP	5	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	CTN	Samples
SN74LVC1G06YZVR	ACTIVE	DSBGA	YZV	4	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	CT N	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



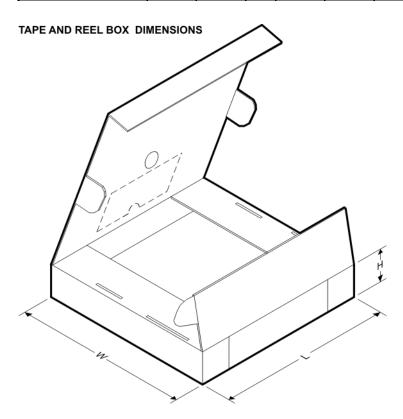
*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G06DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G06DBVR	SOT-23	DBV	5	3000	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G06DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LVC1G06DBVR	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G06DBVRG4	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G06DBVT	SOT-23	DBV	5	250	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G06DBVT	SOT-23	DBV	5	250	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
SN74LVC1G06DBVT	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G06DBVT	SOT-23	DBV	5	250	178.0	9.2	3.3	3.23	1.55	4.0	8.0	Q3
SN74LVC1G06DBVTG4	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
SN74LVC1G06DCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
SN74LVC1G06DCKR	SC70	DCK	5	3000	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G06DCKR	SC70	DCK	5	3000	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G06DCKT	SC70	DCK	5	250	178.0	9.2	2.4	2.4	1.22	4.0	8.0	Q3
SN74LVC1G06DCKT	SC70	DCK	5	250	180.0	8.4	2.47	2.3	1.25	4.0	8.0	Q3
SN74LVC1G06DPWR	X2SON	DPW	5	3000	178.0	8.4	0.91	0.91	0.5	2.0	8.0	Q3
SN74LVC1G06DRLR	SOT-5X3	DRL	5	4000	180.0	9.5	1.78	1.78	0.69	4.0	8.0	Q3
SN74LVC1G06DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

24-Jul-2020

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74LVC1G06DRYR	SON	DRY	6	5000	180.0	9.5	1.15	1.6	0.75	4.0	8.0	Q1
SN74LVC1G06DSFR	SON	DSF	6	5000	180.0	9.5	1.16	1.16	0.5	4.0	8.0	Q2
SN74LVC1G06YZPR	DSBGA	YZP	5	3000	178.0	9.2	1.02	1.52	0.63	4.0	8.0	Q1
SN74LVC1G06YZVR	DSBGA	YZV	4	3000	178.0	9.2	1.0	1.0	0.63	4.0	8.0	Q1



*All dimensions are nominal

All ulfriensions are nominal							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G06DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G06DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G06DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G06DBVR	SOT-23	DBV	5	3000	202.0	201.0	28.0
SN74LVC1G06DBVRG4	SOT-23	DBV	5	3000	180.0	180.0	18.0
SN74LVC1G06DBVT	SOT-23	DBV	5	250	202.0	201.0	28.0
SN74LVC1G06DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G06DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G06DBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G06DBVTG4	SOT-23	DBV	5	250	180.0	180.0	18.0
SN74LVC1G06DCKR	SC70	DCK	5	3000	180.0	180.0	18.0
SN74LVC1G06DCKR	SC70	DCK	5	3000	202.0	201.0	28.0
SN74LVC1G06DCKR	SC70	DCK	5	3000	180.0	180.0	18.0

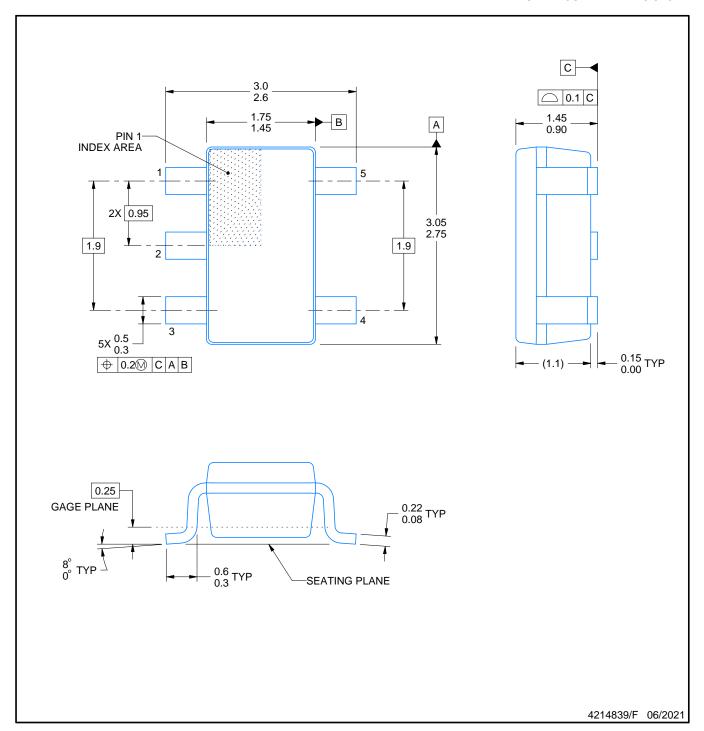
PACKAGE MATERIALS INFORMATION

24-Jul-2020

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74LVC1G06DCKT	SC70	DCK	5	250	180.0	180.0	18.0
SN74LVC1G06DCKT	SC70	DCK	5	250	202.0	201.0	28.0
SN74LVC1G06DPWR	X2SON	DPW	5	3000	205.0	200.0	33.0
SN74LVC1G06DRLR	SOT-5X3	DRL	5	4000	184.0	184.0	19.0
SN74LVC1G06DRLR	SOT-5X3	DRL	5	4000	202.0	201.0	28.0
SN74LVC1G06DRYR	SON	DRY	6	5000	184.0	184.0	19.0
SN74LVC1G06DSFR	SON	DSF	6	5000	184.0	184.0	19.0
SN74LVC1G06YZPR	DSBGA	YZP	5	3000	220.0	220.0	35.0
SN74LVC1G06YZVR	DSBGA	YZV	4	3000	220.0	220.0	35.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SMALL OUTLINE TRANSISTOR



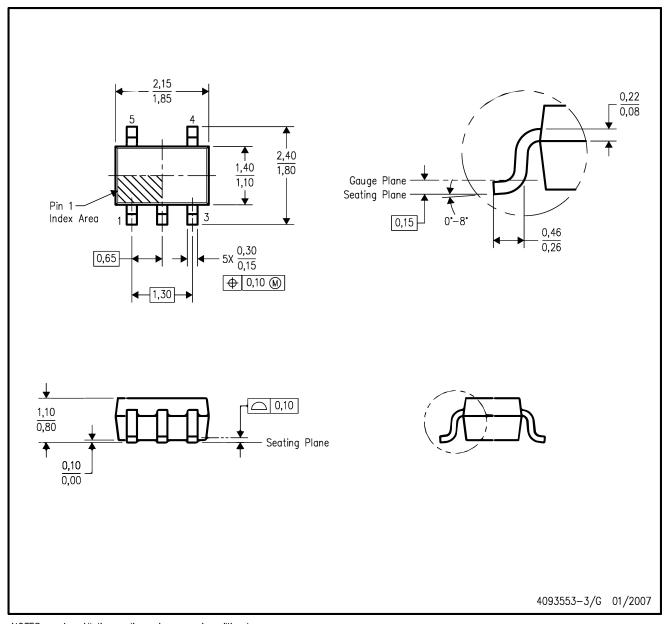
NOTES: (continued)

^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.

DCK (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE

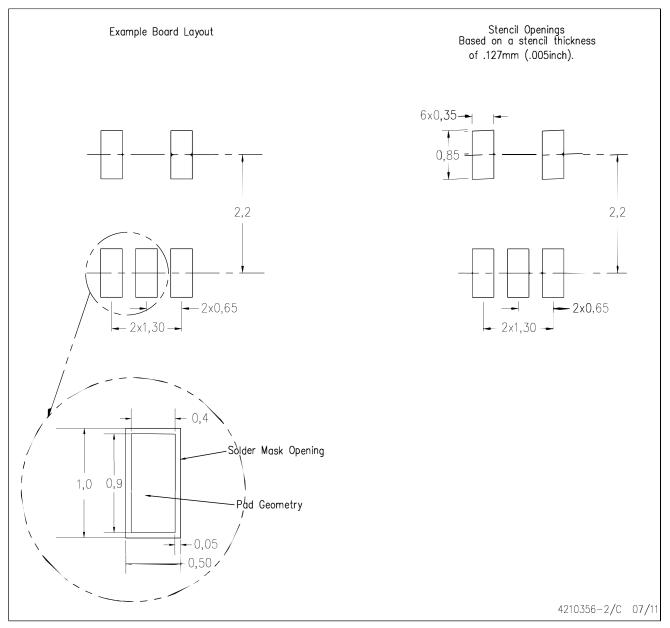


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.

DCK (R-PDSO-G5)

PLASTIC SMALL OUTLINE

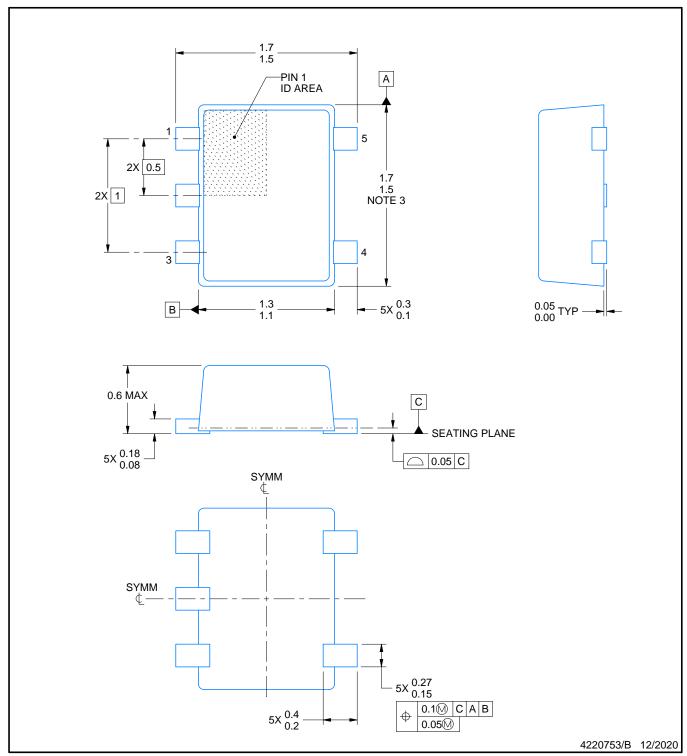


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



PLASTIC SMALL OUTLINE



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-293 Variation UAAD-1

PLASTIC SMALL OUTLINE



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

PLASTIC SMALL OUTLINE



NOTES: (continued)

^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





NOTES:

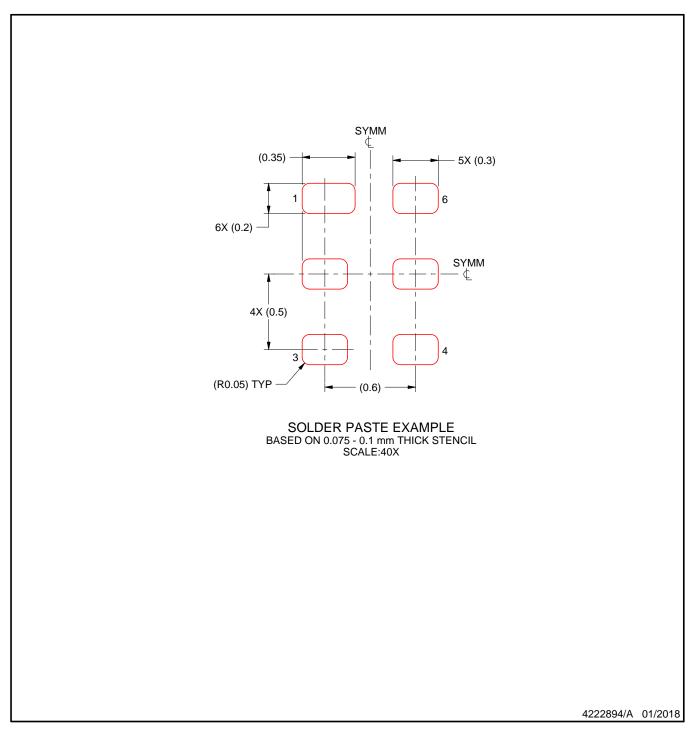
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



NOTES: (continued)

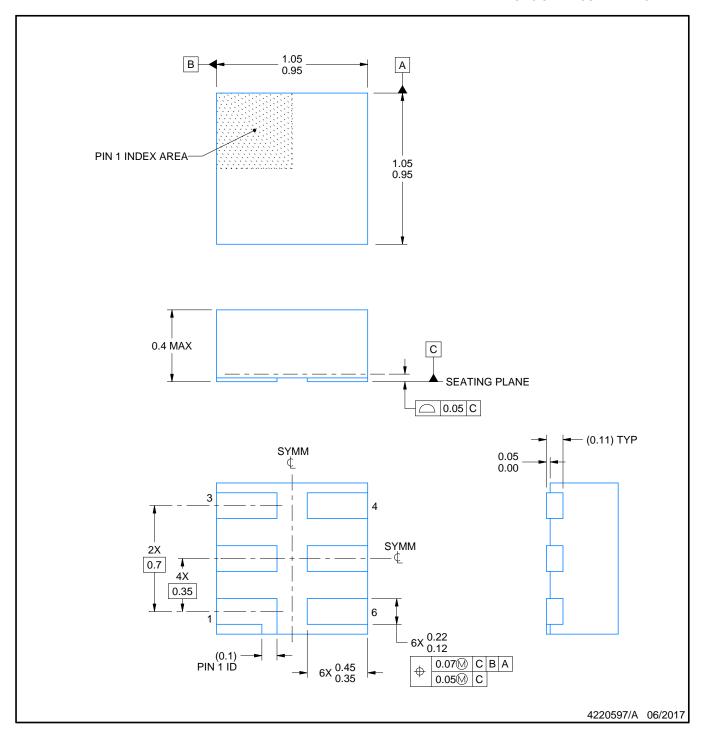
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/slua271).



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



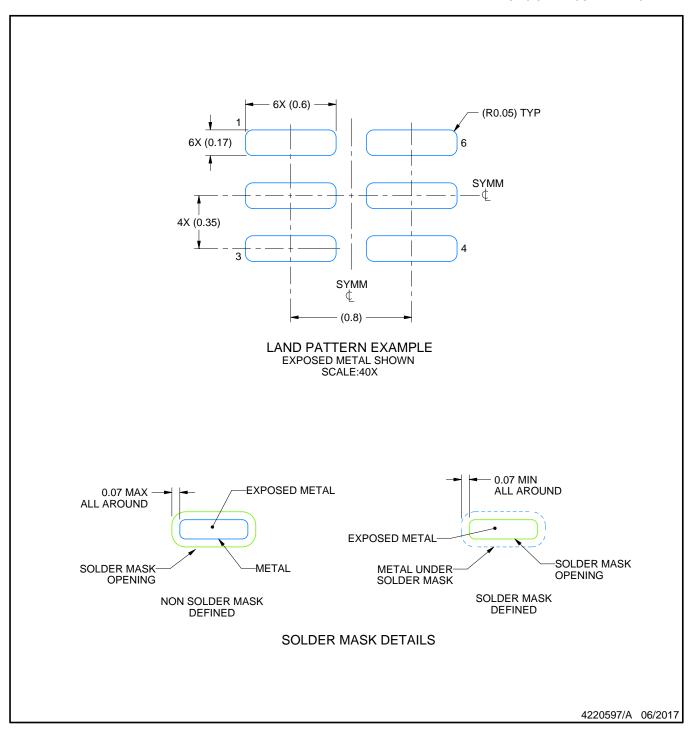


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

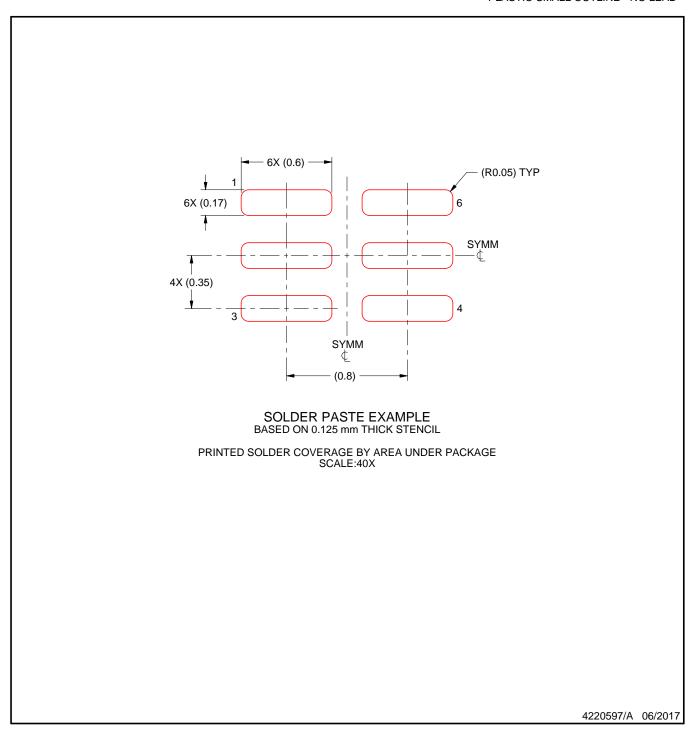
 2. This drawing is subject to change without notice.

 3. Reference JEDEC registration MO-287, variation X2AAF.



NOTES: (continued)

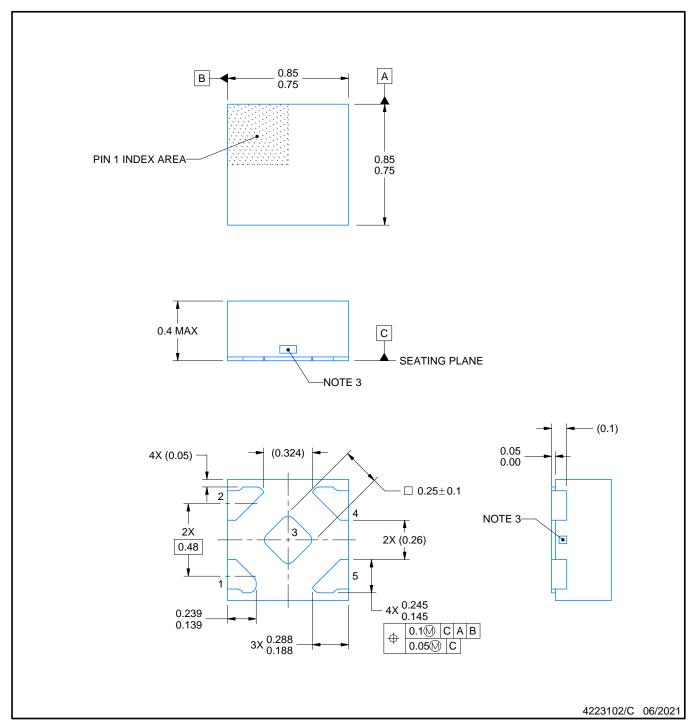
4. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



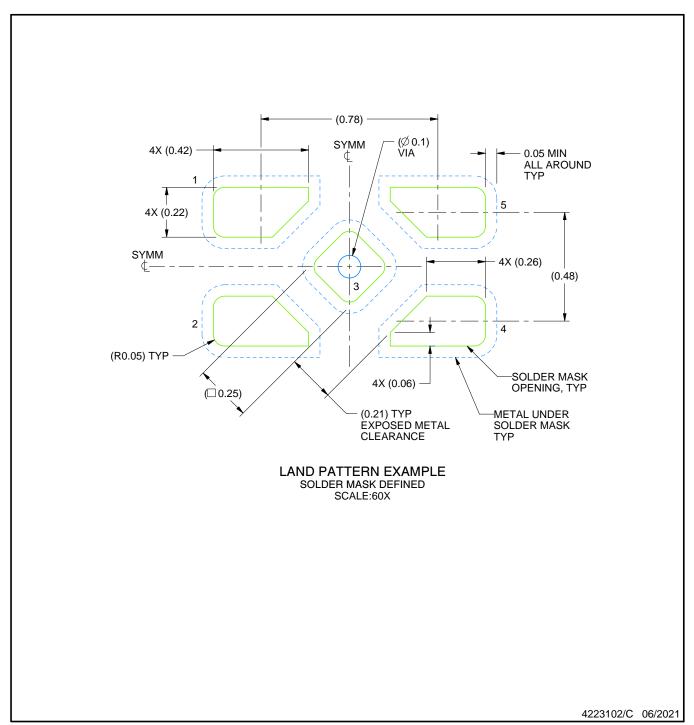




NOTES:

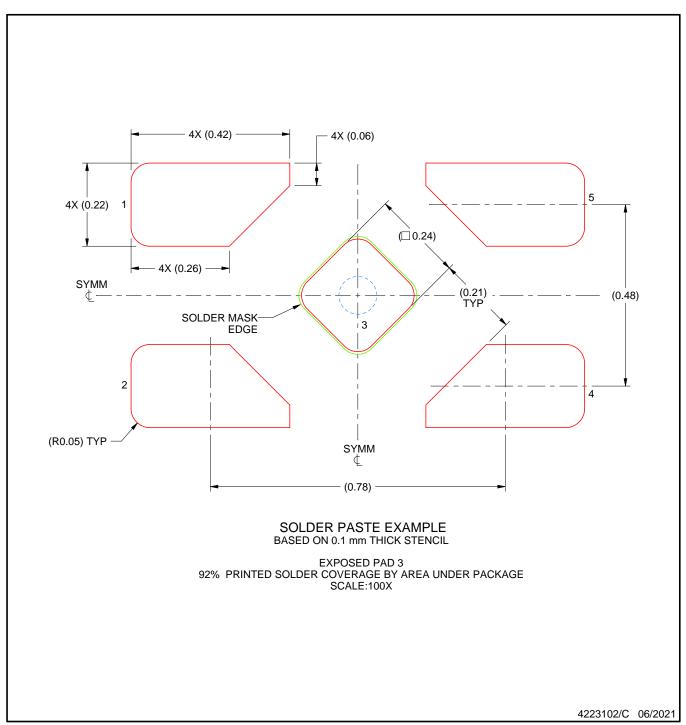
- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.
- 3. The size and shape of this feature may vary.



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, refer to QFN/SON PCB application note in literature No. SLUA271 (www.ti.com/lit/slua271).



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



DIE SIZE BALL GRID ARRAY

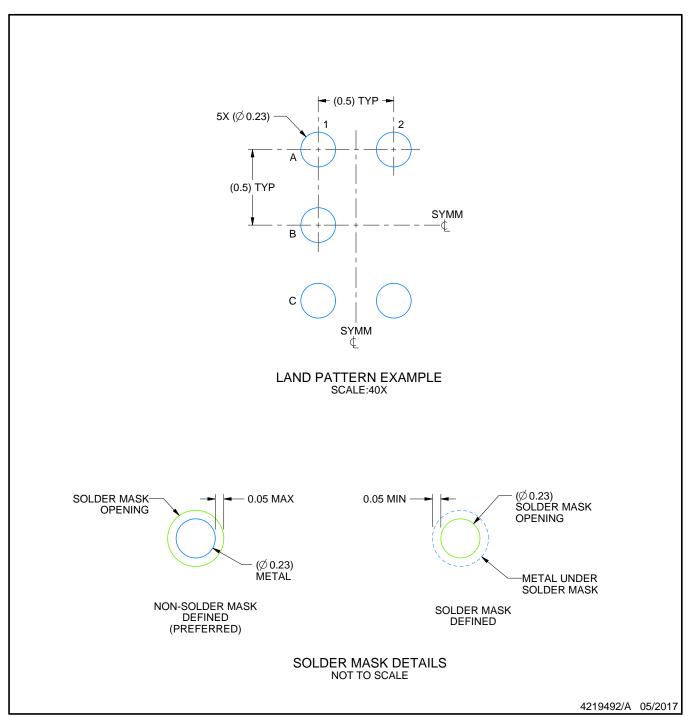


NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

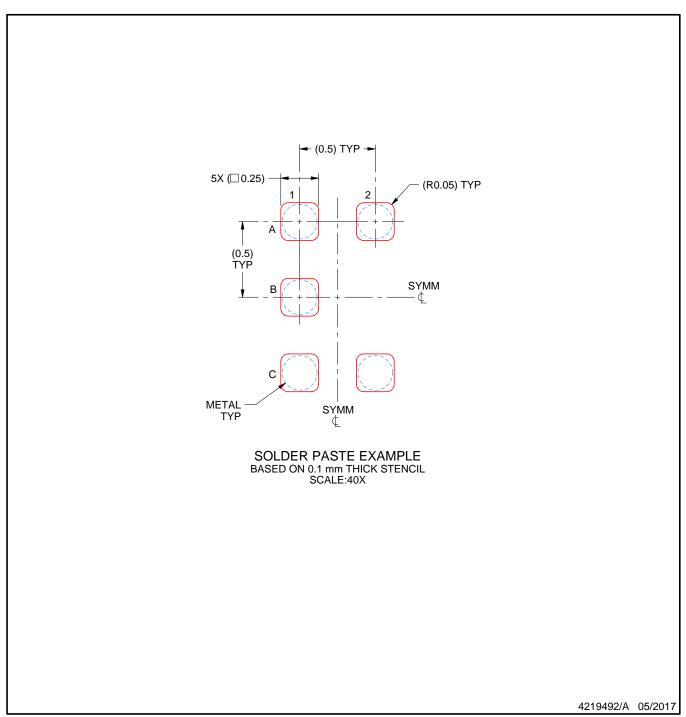
DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).

DIE SIZE BALL GRID ARRAY

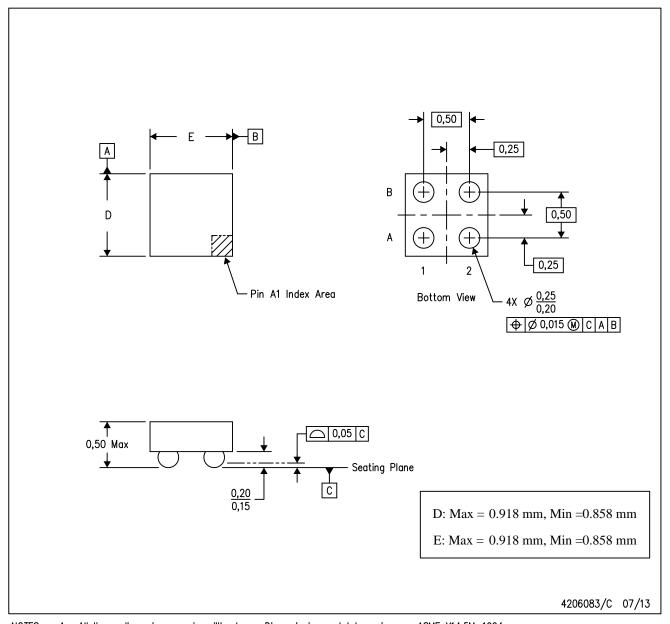


NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

YZV (S-XBGA-N4)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.

- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.